# -13A, -40V P-CHANNEL POWER MOSFET

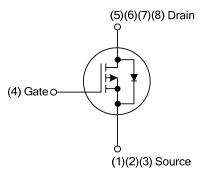
#### **■** DESCRIPTION

The UTC **UTT13P04-H** is a P-channel power MOSFET using UTC's advanced technology to provide the customers with high switching speed and a minimum on-state resistance. It can also withstand high energy in the avalanche.

#### ■ FEATURES

- \*  $R_{DS(ON)}$  < 12 m $\Omega$  @  $V_{GS}$ =-10V,  $I_{D}$ =-12A  $R_{DS(ON)}$  < 17 m $\Omega$  @  $V_{GS}$ =-4.5V,  $I_{D}$ =-12A
- \* Improved dv/dt capability
- \* Fast switching
- \* Green device available

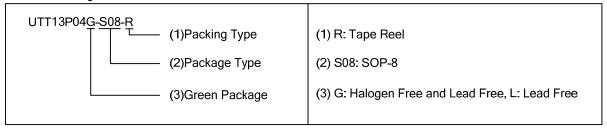
#### ■ SYMBOL



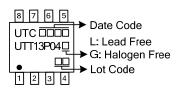
### **■ ORDERING INFORMATION**

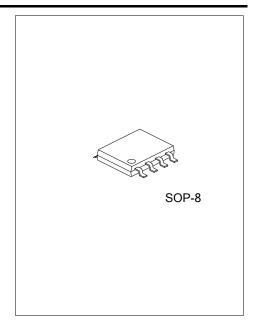
Ordering Number		Daakaga	Pin Assignment							Dooking		
Lead Free	Halogen Free	Package	1	2	3	4	5	6	7	8	Packing	
UTT13P04L-S08-R	UTT13P04G-S08-R	SOP-8	S	S	S	G	D	D	D	D	Tape Reel	

Note: Pin Assignment: G: Gate D: Drain S: Source



#### MARKING





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## ■ ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT	
Drain-Source Voltage		$V_{DSS}$	-40	V	
Gate-Source Voltage		$V_{GSS}$	±20	V	
Continuous Drain Current	Continuous	$I_D$	-13	Α	
Pulsed Drain Current	Pulsed (Note 2)	$I_{DM}$	-39	Α	
Avalanche Energy, Single Pulsed (Note 3)		E <sub>AS</sub>	58	mJ	
Power Dissipation		$P_{D}$	2.5	W	
Junction Temperature		TJ	+150	°C	
Storage Temperature Range		T <sub>STG</sub>	-55 ~ <b>+</b> 150	°C	

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

- 2. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 3. L=-0.1mH,  $I_{AS}$ =-34A,  $V_{DD}$ =20V,  $R_{G}$ =25  $\Omega$ , Starting  $T_{J}$ =25°C

#### ■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	$\theta_{JA}$	50	°C/W

Note: The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.

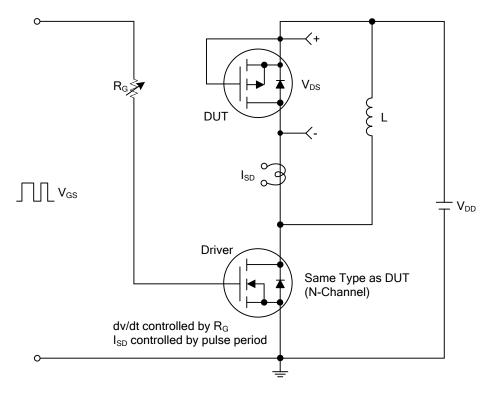
## ■ ELECTRICAL CHARACTERISTICS (T<sub>J</sub> =25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT		
OFF CHARACTERISTICS									
Drain-Source Breakdown Voltage		$BV_{DSS}$	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	-40			V		
Drain-Source Leakage Current		$I_{DSS}$	V <sub>DS</sub> =-40V, V <sub>GS</sub> =0V			-1	μΑ		
Gate-Source Leakage Current	Forward	I <sub>GSS</sub>	V <sub>DS</sub> =0V ,V <sub>GS</sub> =+20V			+100	nA		
Gale-Source Leakage Current	Reverse		V <sub>DS</sub> =0V ,V <sub>GS</sub> =-20V			-100	nA		
ON CHARACTERISTICS									
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$ , $I_D=250\mu A$	-1.0		-3.0	V			
Drain-Source On-State Resistance		RDOVONI	V <sub>GS</sub> =-10V, I <sub>D</sub> =-12A			12	mΩ		
			V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-12A			17	mΩ		
DYNAMIC PARAMETERS									
nput Capacitance		C <sub>ISS</sub>			2900		pF		
Output Capacitance		Coss	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V, f=1.0MHz		330		pF		
Reverse Transfer Capacitance		$C_{RSS}$			220		pF		
SWITCHING PARAMETERS									
Total Gate Charge (Note 1)		$Q_G$	V <sub>DS</sub> =-32V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-13A		58		nC		
Gate to Source Charge		$Q_GS$	$I_G$ =-1mA (Note 1, 2)		14		nC		
Gate to Drain Charge		$Q_GD$	IG IIIA (Note 1, 2)		12		nC		
Turn-on Delay Time (Note 1)		t <sub>D(ON)</sub>			28		ns		
Rise Time		$t_R$	$V_{DD}$ =-20V, $V_{GS}$ =-10V, $I_{D}$ =-13A,		70		ns		
Turn-off Delay Time		t <sub>D(OFF)</sub>	R <sub>G</sub> =-25Ω (Note 1, 2)		192		ns		
Fall-Time		$t_{F}$			170		ns		
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS									
Maximum Body-Diode Pulsed Current		Is				-13	Α		
Drain-Source Diode Forward Voltage (Note 1)		I <sub>SM</sub>				-39	Α		
Maximum Body-Diode Continuous C	$V_{SD}$	I <sub>S</sub> =-12A, V <sub>GS</sub> =0V			-1.2	V			

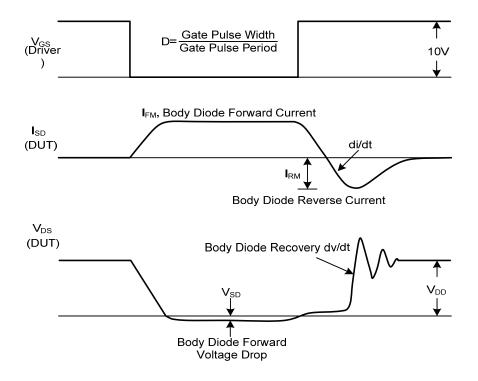
Note: 1. Pulse Test : Pulse width ≤ 400µs, Duty cycle ≤ 2%.

2. Essentially independent of operating temperature.

## ■ TEST CIRCUITS AND WAVEFORMS

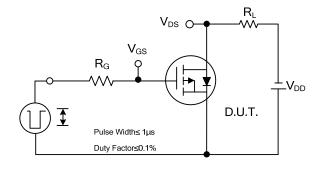


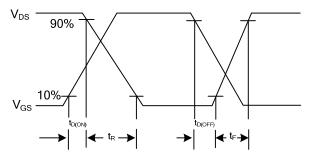
Peak Diode Recovery dv/dt Test Circuit



Peak Diode Recovery dv/dt Waveforms

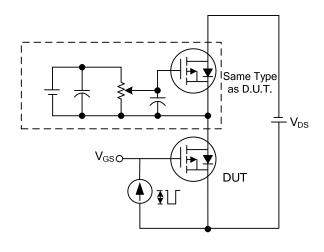
## ■ TEST CIRCUITS AND WAVEFORMS

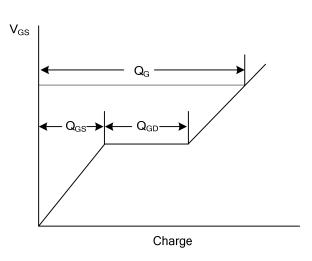




**Switching Test Circuit** 

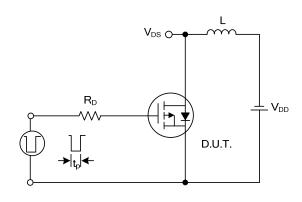
**Switching Waveforms** 

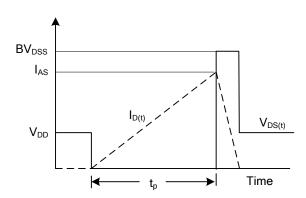




**Gate Charge Test Circuit** 

**Gate Charge Waveform** 

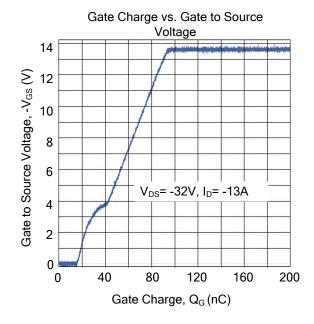


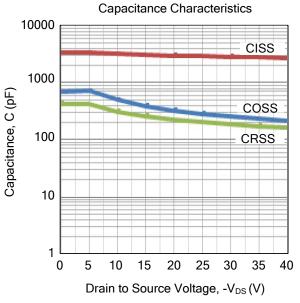


**Unclamped Inductive Switching Test Circuit** 

**Unclamped Inductive Switching Waveforms** 

#### ■ TYPICAL CHARACTERISTICS





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